Static and Dynamic Piezopotential Modulation in Piezo-Electret Gated MoS₂ Field-Effect Transistor

Jing Zhao,† Zheng Wei,‡ Qian Zhang,† Hua Yu,‡ Shuopei Wang,‡ Xixi Yang,† Guoyun Gao,† Shanshan Qin,† Guangyu Zhang,*§ Qijun Sun,*†∥ and Zhong Lin Wang*†∥

†Beijing Institute of Nanoenergy and Nanosystems, Chinese Academy of Sciences, Beijing 100083, China
‡Beijing National Laboratory for Condensed Matter Physics and Institute of Physics, Chinese Academy of Sciences, Beijing 100190, China
§Center on Nanoenergy Research, School of Physical Science and Technology, Guangxi University, Nanning 530004, China
∥Center on Nanoenergy Research, School of Physical Science and Technology, Guangxi University, Nanning 530004, China

Supporting Information

ABSTRACT: The piezotronic effect links the mechanical stimuli with various semiconductor devices, promising for low-power-consuming electronic devices, sensitive sensors, and interactive control systems. The persistent requirement for external strains in piezotronic modulation may hinder its application in some circumstances (such as devices on rigid substrate or complicated synergistic piezoelectric modulation on multidevice). Here, we propose an efficient method to realize piezoelectric modulation of optical and electrical properties of MoS₂ FET in both static and dynamic manner, expanding the application of piezotronics. Through capacitive coupling between piezo-electret and MoS₂ FET, the remanent piezopotential can efficiently tune the Fermi level of MoS₂, programming the initial electrical property for subsequent fabrication of sophisticated devices. The external strain can induce enhanced piezo-potentials to further affect the energy band bending of MoS₂ channel, giving rise to high-performance strain sensors (large gauge factor ∼4800, fast response time ∼0.15 s, and good durability >1000 s). The proposed static and dynamic piezopotential tuned MoS₂ FET is easy to extend to devices based on other materials, which is highly desired in tunable sensory systems, active flexible electronics, and human–machine interface.

KEYWORDS: piezopotential modulation, MoS₂ FET, optical and electric properties, piezo-electret, mechanical sensors

Piezotronic effect is to use the piezoelectric polarization charges to serve as a “gate” for controlling the transport in semiconductors, especially at a metal–semiconductor contact (M–S contact) or p–n junction. It is highly desirable and compatible in ultrasensitive nanoforce sensors and biosensors, high-resolution adaptive sensing arrays, piezotronic transistors, and optoelectronic device modulations. Piezopotential is an intrinsic inner-crystal field induced by electric dipole moments, which is originated from nonmobile ions on crystal lattice sites or polar molecular groups with asymmetric charge surroundings. Therefore, piezopotential can be maintained as long as the piezoelectric material is subjected to external strains, that is, piezoelectric polarization requires persistent external strain. As the piezopotential is in linear dependence with applied strain, the piezoelectric effect is beneficial for the dynamic response of the piezotronic devices, such as mechanical sensing, actuation, interactive modulation, and energy transduction. Meanwhile, the static piezoelectric modulation of electrical properties free from external strains is also important, yet uneasy to be realized in some specific situations (such as devices on rigid substrate or multidevices operation under synergistic piezoelectric modulation). Therefore, broadening the semiconductor device modulation modes by piezo-polarization in both

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static and dynamic manner is critical from both materials and device structure aspects.\(^7\)−\(^10\)

Transition-metal dichalcogenides (TMDCs) have attracted significant attentions for soft electronics due to their excellent electrical, optical, thermal, and mechanical properties.\(^11\)−\(^15\) As a representative of TMDCs, molybdenum disulfide (MoS\(_2\)) consists of S−Mo−S sandwiched atomic units in a hexagonal-structured crystal, exhibiting a 1.9 eV direct band gap for the monolayer.\(^16\) The mobility and on/off ratios of MoS\(_2\) field-effect transistor (FET) can be achieved up to 1000 cm\(^2\)·V\(^−1\)·s\(^−1\) (at low temperature) and 10\(^8\), respectively.\(^17\) Its superior resistance to short-channel effects, attractive electrical performance characteristics, high electrostatic control and high surface-to-volume ratio promise wide applications for flexible optoelectronic devices, ultrasensitive sensors, supercapacitors, catalysis, etc.\(^18\)−\(^25\)

According to the noncentral symmetry of its crystal structures, the intrinsic piezoelectricity of MoS\(_2\) is theoretically predicted and experimentally demonstrated in the odd-layer samples by mechanical exfoliation.\(^16\) The mobility and on/off ratios of MoS\(_2\) field-effect transistor (FET) can be achieved up to 1000 cm\(^2\)·V\(^−1\)·s\(^−1\) (at low temperature) and 10\(^8\), respectively.\(^17\) Its superior resistance to short-channel effects, attractive electrical performance characteristics, high electrostatic control and high surface-to-volume ratio promise wide applications for flexible optoelectronic devices, ultrasensitive sensors, supercapacitors, catalysis, etc.\(^18\)−\(^25\)

However, the piezotronic modulation is elusive to achieve due to the difficulty in both accurate preparation of odd-layer MoS\(_2\) in single crystal and construction of perfect metal contacts. The piezoresistive effect accompanied with mechanical strains can also change the band structure to confound with piezotronic effect, which may hinder the piezotronic modulation in sophisticated devices. Therefore, it is critical to develop a simple and universal method to achieve the facile piezoelectric modulation of 2D materials based semiconductor devices. Capacitive coupling by connecting piezoelectric materials and semiconductor devices in series offers an alternative way to control the charge transport in semiconductor devices.\(^29\)−\(^32\)

Different types of piezoelectric materials (such as piezoelectrets, piezoelectric, and ferroelectric materials) are facile to be integrated to realize efficient piezoelectric modulation, which can complement and expand the application of piezotronics.\(^33\)−\(^35\)

In this work, a piezo-electret polymer was capacitively coupled with MoS\(_2\) FET to achieve both static and dynamic piezoelectric tuning of the transport properties. On one hand, the remnant polarization induced by aligned dipoles in a piezo-electret could statically tune the Fermi level of MoS\(_2\) channel, realizing broad modulation of the initial electrical performance of MoS\(_2\) FET by 2 orders of magnitude through changing the downward prepolarization to upward direction. On the other hand, the external tensile/compressive strain can further enhance/weaken the aligned dipoles in a piezo-electret and result in different piezo-potentials to effect the energy band bending of MoS\(_2\) channel, giving rise to highly sensitive strain sensor (gauge factor \(\sim 4800\)). The on/off switch was also demonstrated to be fast (0.15 s) and stable (over 1000 s).

Figure 1. Static electric regulation of the MoS\(_2\) FET by the P(VDF-TrFE) film as a gate material. (a) The schematic diagram of polarization, piezoelectricity, and semiconductor coupling. (b) The schematic diagram of the device with flexible P(VDF-TrFE) film on PET substrate. (c) The optical image of the MoS\(_2\) pattern with source–drain electrodes (left). The right panel is the AFM image of the MoS\(_2\) channel with a thickness of \(\sim 0.7\) nm. (d) The remanent voltage of P(VDF-TrFE) is \(\sim 1.9\) V after polarization, and the piezo-potential increases with the strain. (e) The output property of the device with channel length and width is \(\sim 20\) μm and \(\sim 5\) μm, respectively. (f) The \(I−V\) curve for the MoS\(_2\) device gated by the P(VDF-TrFE) piezo-electret under opposite polarized voltages.
Under dynamic modulation, the on/off current ratio exceeded 4 orders of magnitude with the external strain varying from −0.3% to 0.2%, which was comparable to the device electrical performance under applied gate bias. Notably, the piezo-potential modulation of the light emission of MoS2 channel was visualized through photoluminescence (PL) spectroscopy. The PL peak of MoS2 showed a significant blue shift of ~14 meV when the strain applied on piezo-electret was increased to 1.2%, similar to the MoS2 light emission control by electric-field gating. Besides, a piezo-electret modulated MoS2 FET with compact structure design and feasible in situ polarization was demonstrated through directly spin-coating a piezo-electret polymer on a MoS2 channel. Piezoelectric polarization by low-voltage bottom gate pulses (<60 V) enabled comparable modulation effects on the initial transport properties of MoS2. The proposed static and dynamic piezoelectric modulation of electrical and optical properties in 2D nanomaterials is of great significance in tunable semiconductor devices, sophisticated flexible electronics, highly sensitive mechanical sensors, and human–machine interface.

RESULTS AND DISCUSSION

Figure 1a shows the basis of pieztronics, an emerging field involving piezo-electricity, semiconductor, and photoexcitation. The three-term coupling (among polarization, semiconducting characteristics, and photoexcitation) implies the piezotronic effect on charge carrier transport and separation/recombination at a contact or junction, which promotes the modulation of the energy band levels and optoelectronic process by mechanical stimuli in a dynamic manner. The proposed piezo-electret gated MoS2 FET further realizes the static modulation of charge transport free from external strain due to the stable remnant potentials in the piezo-electret gate, which complements the three-term coupling and expands a broader application of pieztronics. The schematic illustration of the piezo-electret gated MoS2 FET is demonstrated in Figure 1b. The uniform and continuous MoS2 films were grown on sapphire by an oxygen-assisted CVD method to avoid multilayer MoS2 film deposition. Then the MoS2 films were transferred to PET substrate with prepatterned Au source–drain electrodes. MoS2 channel was defined to be 20 μm by standard photolithography and reactive ion etching (RIE). The atomic force microscope (AFM) image of the device demonstrates the monolayer property (~0.7 nm) of the MoS2 channel with clean surface (Figure 1c). To enhance the electrostatic field effect on a MoS2 channel induced by piezo-electret, high-κ Al2O3 (30 nm) was selected as the gate dielectric layer by atomic layer deposition (ALD). Indium tin oxide (ITO) was sputtered as an extended gate electrode for capacitive coupling between piezo-electret and MoS2 FET. Among the piezoelectric polymer family, poly-(vinylidenefluoride-co-trifluoroethylene) (P(VDF-TrFE)) with VDF content between 50% and 80% presents a preferential ferroelectric β-phase due to the addition of a third fluoride into the TrFE monomer unit, which increased the steric hindrance and induced an all-trans conformation (corresponding to the ferroelectric β-phase). In this work, P(VDF-TrFE) (70/30) was utilized as the piezo-electret to modulate the transport properties of MoS2 FET through static remnant polarization after poling process and dynamic piezo-potentials under different external strains. The P(VDF-TrFE) film as a top-gate for the device needed to be polarized in advance. The prepolariation rearranged the dipoles in the P(VDF-TrFE) film in an oriented alignment, exhibiting a remnant piezo-potential (the aligned dipoles could be maintained at a certain extent for a long time after removing the external voltage). As shown in Figure 1d, the open circuit voltage produced by P(VDF-TrFE) sandwiched between ITO and Au electrodes shows a linear increment according to the applied strain varied from 0% to 0.5%. In particular, the remnant potential is equivalent to 1.9 V without applying any strains, attributing to the aligned dipole moments after polarization (i.e., positive hydrogen groups and negative fluorine groups formed in an all-trans ferroelectric β-phase).

Electrical properties of the MoS2 FET were first characterized by a semiconductor analysis system (Agilent B1500) in atmospheric environment. Typical output curves of MoS2 FET were shown in Figure 1e. The drain current (I_D) was increased from 0.3 pA to 6.27 μA with a gate voltage increase from −3 to 3 V at a drain voltage (V_D) of 3 V. The linear I–V characteristics at V_D below 1 V demonstrated the good contact between source–drain electrodes and MoS2 channel. Due to the high dielectric constant of the Al2O3, the on/off ratio was nearly 105 at low gate voltages sweeping from −3 to 3 V (Figure S1). The mobility was calculated to be ~30 cm2·V−1·s−1 with the channel length and width at 20 and 5 μm, respectively. The equivalent circuit of the piezo-electret gated MoS2 FET is a P(VDF-TrFE) capacitor in series connection with an Al2O3 capacitor (Figure S2). Therefore, the charges repelled by the piezo-potential cannot be compensated through the series connection, which imposes an electrostatic field effect on the MoS2 channel. The equivalent gate bias (V_G_eq) under external strains is related to the open circuit voltage (V_piezo-electret) produced by the piezo-electret following V_G_eq = (C_piezo-electret/C_oxide) × V_piezo-electret where C_piezo-electret and C_oxide are the capacitances of P(VDF-TrFE) and Al2O3, respectively. We defined P(VDF-TrFE) without polarization as the pristine state, dipole moments aligned downward as the positive state (P_positive), and dipole moments aligned upward as the negative state (P_negative), respectively (Figure S3). After the polarization of P(VDF-TrFE) through applying different polarizing voltages, downward alignment of the dipoles induced an equivalent positive gate bias applied to the MoS2 channel, which enhanced the electrons in the MoS2 channel, bent the conduction band of MoS2 downward, and led to a higher current level compared with the pristine state. In contrast, upward alignment of the dipoles induced an equivalent negative gate bias applied to the MoS2 channel, which resulted in the conduction band of MoS2 bending upward and led to a lower current level compared with the pristine state (Figure 1f). Relevant band diagram illustration with opposite prepolarization is shown in the bottom panel of Figure S3. The I_D of MoS2 FET shows a 2 orders of magnitude variation (V_D = 1 V) under opposite polarization directions. The remnant piezo-potential in the prepolarized piezo-electret film can effectively affect the Fermi level of MoS2 channel and adjust the current level of the device, which provides an efficient approach to programming the initial electrical performance of the electronic devices for subsequent sophisticated applications.

To verify the equivalent gating effect of piezo-potential, we characterized the optical properties of MoS2 under different external strains. Different from the top-gate device structure on PET substrate, the monolayer MoS2 was transferred on SiO2/
Si substrate and modulated by P(VDF-TrFE) through the bottom SiO2 dielectric to ensure the direct exposure of the MoS2 surface to the laser (Figure 2a). The detailed structure is shown in Figure S2. The Raman spectrum of MoS2 without piezo-electret modulation (Figure S4a) confirms the MoS2 film grown by CVD is monolayer according to the Raman shift at 20 cm$^{-1}$ between two typical Raman peaks: $E_{2g}$ (384 cm$^{-1}$) and $A_{1g}$ (404 cm$^{-1}$).38 In Figure S4b, the two typical PL spectra peaks of the MoS2 sample are observed at 663 and 613 nm, respectively. These two peaks correspond to the direct optical transitions at the Brillouin zone K-point and the spin–orbital splitting of the valence band, respectively. Therefore, the two resonances corresponding to the energy $\sim$1.88 eV and $\sim$2.03 eV are pronounced as $A_1$ and $B_1$ excitons.39,40 Slight red shift of the $A_1$ peak with our MoS2 sample compared with the suspended MoS2 ($\sim$1.90 eV) was mainly caused by the trapped charges doping from substrate.16

According to the piezoelectric property of the P(VDF-TrFE), external strains can further enhance/weaken the aligned dipole moments, representing increased/decreased piezopotentials. Figure 2b demonstrates that the open circuit voltages have a stepped increment under increased strains after positive polarization. The PL spectrum of piezo-electret gated MoS2 FET under tensile/compressive strain is shown in Figure 2c. When the applied strain was increased from $-0.2\%$ (compression) to 1.2% (tension), an apparent blue shift of the $A_1$ excitons (from $\sim$663 nm to $\sim$657 nm) with enhanced intensity was observed due to the accumulation of free electrons in monolayer MoS2. The PL shift was attributed to that the accumulated free electrons by piezopotential alleviated the passivation of MoS2 surface states deriving from trapped charges at the MoS2/SiO2 interfaces, similar to the effect of directly applying positive gate bias.41 The detailed PL shifts characterized under relevant strains are stable as shown in Figure S5a. The extracted $A_1$ peaks were observed to represent a blue shift of 14 meV, while the $B_1$ peak had no obvious change when the strain varied from $-1.2\%$ to 1.2% (Figure 2d). The unobvious shift of $B_1$ peak position under different external strains may be attributed to the mild influence of piezo-potential on the spin–orbital splitting of the MoS2 valence band. In addition, the intensity of the $A_1$ peak decreased obviously with the increased strain, further confirming that the piezo-potential effectively alleviated the charge trapping deriving from substrate doping. In Figure S5b, the invariant Raman shift declares that piezo-potential induced by P(VDF-TrFE) has no influence on in-plane vibration and out-of-plane phonon coupling mode of MoS2. The optical properties of the piezo-electret gated MoS2 demonstrated that the piezo-potentials induced by external strains were equivalent to gate biases applied to MoS2 FET.

After investigating the optical properties of MoS2 imposed by the piezo-potential from P(VDF-TrFE), electrical properties of the piezo-electret gated MoS2 FET under different strains were characterized in detail. Even though the monolayer MoS2 had a small piezoelectric output theoretically, the MoS2 film we grew by CVD method contained some grain boundaries, leading to an ignorable piezoelectric effect from MoS2 itself. Therefore, the MoS2 FET without P(VDF-TrFE) regulation had a stable electrical property even under a strain of $\sim$1%.18 Due to the piezoelectric property of the polarized P(VDF-TrFE), the piezopotential was linearly proportional to the applied strains ($\varepsilon$) according to $V_{\text{piezo-electret}} = \varepsilon/d$, as illustrated in Figure S6a ($d$ is the piezoelectric coefficient). The induced piezo-potential also represents good stability and long-term durability (Figure S6b,d). As shown in Figure 3a,c, the impositions of tensile and compression strains to the piezo-electret were equivalent to applying positive and negative gate biases to the MoS2 FET, resulting in corresponding band...
bends compared with the device in a relax state (Figure 3b). The ineluctable charge trapping from substrate shifted the threshold voltage of MoS2 FET to the negative direction, giving rise to an enhanced electrons density in the MoS2 channel ($I_D \sim 0.1 \mu A$) at zero gate bias (Figure S1). To achieve higher on/off ratio of the piezo-electret gated MoS2 FET, we reasonably polarized P(VDF-TrFE) in the positive state (dipoles moment aligned upward), which induced further accumulation of electrons in MoS2 ($I_D \sim 1.0 \mu A$, Figure 3e). Thus, applying compressive strain (equivalent to negative gate bias) enabled more capacity to deplete the electrons in MoS2 channel and realized highly efficient modulation on MoS2 transport properties. Figure 3d shows the output performance of piezo-electret gated MoS2 FET. When the strain was increased from $-0.15\%$ to $0.2\%$, the output current of the MoS2 FET increased from $\sim 3.8 \text{ nA}$ to $\sim 0.7 \mu A$ at $V_D = 1 \text{ V}$. The output performance of piezo-electret gated MoS2 FET with wider $V_D$ sweeping from $-3 \text{ V}$ to $3 \text{ V}$ is shown in Figure S7. The transfer characteristics ($I_D$ vs strain) of piezo-electret gated MoS2 FET is shown in Figure 3e. Through controlling the applied external strain, the device was able to switch from high resistance to low resistance state with $I_D$ varying from $10^{-10}$ to $10^{-6} \text{ A}$. The on/off ratio tuned by strain was more than $10^6$, comparable to the device driven by applied gate voltage in Figure S1. The efficient piezo-potential gating through capacitive coupling was attributed to the high dielectric constant of Al2O3 and appropriate static piezo-potential programming on the initial current level of MoS2 FET. The nonlinear behavior of the output current as a function of strain in Figure 3e was explained as follows: The P(VDF-TrFE) film in positive state (dipoles moments pointing to the ground, Figure 3b) after prepolarization enhanced the electrons in MoS2 channel, resulting in an increased $I_D$ of $1.0 \mu A$ at $V_D = 1 \text{ V}$ compared with the $I_D$ ($\sim 0.1 \mu A$) of pristine MoS2 FET in Figure S1. When P(VDF-TrFE) film was subjected to tensile strain (Figure 3a), an enhanced positive

Figure 3. Dynamic electrical regulation of the MoS2 FET by bending P(VDF-TrFE). (a–c) Corresponding charge distribution of the piezo-electret for tensile, relax, and compression conditions. (d) The output curves of the piezo-electret gated MoS2 FET under different strains. (e) The transfer curve of piezo-electret gated MoS2 FET ($I_D$ vs $\varepsilon$). (f, g) Dynamic electrical properties of the MoS2 FET under tensile ($0.1\%$) and compression strain ($-0.1\%$) pulses. (h) Time response of the MoS2 FET under strain. (i) The stability of MoS2 FET after $10^5$ s measurement.
piezo-potential compared with the initial positive state was coupled to MoS$_2$ FET. It further bent the energy band of MoS$_2$ downward and led to an increment of $I_{D}$ from 1.0 $\mu$A to 1.1 $\mu$A (red region). In contrast, when P(VDF-TrFE) film was subjected to compressive strain (Figure 3c), a negative piezo-potential was coupled to MoS$_2$ FET. It depleted the electrons in the MoS$_2$ channel, bent the energy band of MoS$_2$ upward, and resulted in an exponential decrement of $I_{D}$ (blue region). When the compressive strain was further increased to $\sim$0.3%, enhanced negative piezo-potential was imposed on MoS$_2$ FET and depleted almost all the free electrons in the MoS$_2$ channel, resulting in the complete cutoff state of MoS$_2$ FET (green region). In this region, the $I_{D}$ was dominated by leakage and charging currents.

As the output currents were associated with the external strain, the piezo-electret gated MoS$_2$ FET was capable of working as a strain sensor. According to the dramatic resistance change (over 10$^6$) under applied strains varying from $-0.3\%$ to 0.2%, the extracted gauge factor (GF or sensitivity) under compressive strain is 4800 with a strain varying from $-0.1\%$ to 0%, while the GF is 250 under a tensile strain from 0% to 0.1% (Figure S8). Notably, the compressive GF achieved in the piezo-electret gated MoS$_2$ FET strain sensor is much higher than the reported ultrahigh GFs of ZnO tribotronic strain sensors ($\sim$1250) and CNT strain sensors ($\sim$1000) and far more than the commercial metal foil strain gauges (2–5), p-type germanium strain sensors (\sim 102), or silicon strain sensors (\sim 125–200).\textsuperscript{12} The dynamic electrical measurements under tensile (0.1%) and compression (\sim 0.1%) strains show reproducible current switching in Figure 3f, respectively ($V_{DD} = 1$ V). The response and decay time are extracted to be $\sim$0.15 s and $\sim$0.25 s (Figure 3h), which is comparable with other strain sensors based on 2D materials. Long-term stability of the strain sensor (over 1000 s) is also confirmed in Figure 3i. Efficient piezo-potential modulation of the electrical properties demonstrated the great potential of the piezo-electret gated MoS$_2$ FET as a strain sensor due to the high sensitivity, fast response time, and excellent repeatability. The demonstrated device architecture occupies extra space due to the piezo-electret patterned on the extended gate. It is important to make a compact design of the piezo-electret gated MoS$_2$ FET for highly integrated device application. Therefore, preparing a piezo-electret conformal on the FET channel in a vertical structure was proposed to provide an alternative route to piezo-potential modulation. As shown in Figure 4a, the 5 wt % P(VDF-TrFE) was spin-coated on the surface of the MoS$_2$ device, resulting in a film thickness at $\sim$300 nm (Figure S9). Then 20 nm Au was deposited as a top-gate electrode. The intrinsic piezo-electret (i.e., ferroelectric) characteristic of the P(VDF-TrFE) provided a way to \textit{in situ} tune the electrical property of the device. Before spin-coating P(VDF-TrFE), typical output and transfer performances of MoS$_2$ FET were first characterized (Figure 4b,c). The on/off ratio and mobility were $\sim$10$^6$ and $\sim$43 cm$^2$-V$^{-1}$-s$^{-1}$, respectively, comparable to the previous results.\textsuperscript{36} A small hysteresis was observed under the bottom gate sweeping in reverse directions from 0 to 60 V (Figure 4d), originating from the substrate doping effect. With the spin-coated P(VDF-TrFE) film on top of the MoS$_2$ channel, the hysteretic window of the device was enlarged to be 35 V due to the instantaneous polarization switch of P(VDF-TrFE) under forward/backward bottom gate sweeping (Figure 4e). The large hysteretic window indicated the feasibility of polarization switching of the top P(VDF-TrFE) layer through bottom gate bias.

From Figure 4e, it is observed that the MoS$_2$ channel can be fully accumulated and depleted at gate voltages of 60 V and $-60$ V, respectively. We reasonably selected pulse voltages at 60 V and $-60$ V (pulse width at 1 s) as the polarization voltages for the positive and negative states of the P(VDF-TrFE) piezo-electret. The positive/negative pulse voltages set
the P(VDF-TrFE) in a persistent positive or negative state due to the remnant piezopotential in the ferroelectric film. Positive polarization (pulse voltage at 60 V) aligned the dipoles in the P(VDF-TrFE) thin film, equivalent to applying a positive top gate to the MoS2 FET. In contrast, negative polarization (pulse voltage at −60 V) induced an opposite poling electrical field for the P(VDF-TrFE), equivalent to a negative gate bias. The large hysteresis in Figure 4e is attributed to the instantaneous polarization switch of P(VDF-TrFE), confirmed by the similar hysteresis windows in Figure S10 (tested with a MoS2 FET with 50 nm thickness PMMA interlayer between MoS2 and P(VDF-TrFE)). This result excluded that the large hysteresis originated from the charge traps at the interface between P(VDF-TrFE) and MoS2. The P(VDF-TrFE) with top electrode also played a role as a capacitor after back-gate voltage pulse polarization, which could be coupled to the MoS2 device, leading to the source–drain current change. In addition, to apply polarized voltage from back-gate, the top-gate electrode provided another way to realize the large hysteresis as demonstrated in the previous study.53 Figure 4f shows the output performance of the compact piezo-electret gated MoS2 FET. After pulse polarizations from bottom gate, the output currents were statically modulated to increase from 6 nA to 60 nA (Vg at 1 V) without any applied gate voltages or external strains. Similar results with Figure 1f reflected comparable static modulation capacity of the compact piezo-electret gated MoS2 FET in lower coercive voltage (<60 V). The in situ modulation of the electrical property in MoS2 FET suggests more potential application in highly integrated flexible electronics. In addition, the observed hysteresis window in the piezo-electret gated MoS2 FET is promising for high-performance nonvolatile memory devices.44

CONCLUSION

In conclusion, we successfully demonstrated the piezopotential modulation of the electron transport properties in MoS2 FET in both a static and dynamic manner. It offered an efficient way to modulate the Fermi level of the MoS2 channel without applying gate voltage (over 105 on/off switching) and represented great significance in high-performance strain sensors (gain factor at ~4800, fast response time of 0.15 s, and good durability over 1000 s). The optical properties of MoS2 under piezopotential modulation were also observed, exhibiting a 14 meV blue shift in the PL peak. The piezo-electret gated MoS2 FET with compact structure design enabled feasible local polarization to achieve excellent static modulation capacity on MoS2 channel. The demonstrated static and dynamic coupling between piezo-potential and semiconducting properties was anticipated to enrich the application of piezotronic effect in efficient semiconductor device modulation, tunable sensory systems, highly integrated matrix, and active multifunctional soft electronics.

As we discussed above, the electromechanical piezotronic effect interlinked the mechanical motions with various semiconductor devices, which gave rise to low-power-consuming wearable devices and interactive electronic systems. Besides the accessible mechanical energy in the surrounding environment, thermal energy originating from temperature gradients and fluctuations is ubiquitous in our daily life. The human body itself is a good source of thermal energy. Instead of a piezo-electret, pyroelectric material with ferroelectric phase (pyro-electret) is also promising to integrate with semiconductor devices to realize the static and dynamic pyroelectric modulation. The pyro-potential produced by temperature variation also shows the capacity of tuning the charge carrier transport and separation/recombination.35 Inspired by the three-term coupling among polarization, semiconductor, and photoexcitation, we suggest the perspective of electrets with piezo-potential, pyro-potential, or combined piezo/pyroelectric potential to couple with nanomaterial-based semiconductor devices (Figure S11). Implemented with the piezo/pyroelectric modulation, the electronics based on an electret may have broader applications in multifunctional sensory systems, highly efficient energy harvesting, human–machine interface, and the Internet of Things (IoT).

METHODS

Materials Preparation. MoS2 synthesis: The monolayer MoS2 film was synthesized in a three-temperature-zone CVD system. Sulfur (Alfa Aesar 99.9%) and molybdenum trioxide (MoO3) (Alfa Aesar 99.999%) were used as precursors and loaded in growth zones I and II, respectively. The 300 nm SiO2/Si substrate was loaded in zone III. The temperatures of the three temperature zones were 115, 560, and 750 °C, respectively. 100 sccm Argon was used as carrier gas, and the pressure of the system was 1.0 Torr during the synthesis process. For the monolayer MoS2 growth without defects and multilayer deposition, 0.5 sccm O2 was bubbled into the tube during the growth process. The whole growth time lasted for 10 min.

Device Fabrication. MoS2 film was first transferred to PET substrate with predeposited Ti/Au (2 nm/30 nm) source–drain electrodes. Photoresist (AZ5214) was spin-coated on the MoS2 film at 4000 r/min speed, and the sample was prebaked at 90 °C for 3 min to remove the solvent. Then the UV exposure was performed for 8 s to pattern the MoS2 channel, and the unnecessary MoS2 was etched by a reaction ion etching (RIE) system. After using the acetone to remove the protective resist, the 30 nm thickness dielectric layer (Al2O3) was deposited by atomic layer deposition (ALD) at 110 °C using Savannah-100 system (Cambridge NanoTech Inc.). In the ALD process, the precursors were H2O (heated to 80 °C) and trimethyl aluminum (TMA) (at room temperature), respectively, while the carrier gas was 20 sccm N2 in high purity. The two precursors were injected in turn, and the pulse times for TMA and H2O were 0.015 and 0.15 s, respectively. Every cycle lasted for 40 s, and the thickness of the layer increased ~0.9 Å. Then 20 nm ITO was deposited as the top-gate and extended electrode for piezo-electret. The P(VDF-TrFE) was precisely spin-coated on the extended ITO electrode with a polymer stencil. After pre-polarization, 30 nm Au was deposited as the top electrode. For the compact piezo-electret gated MoS2 FET, after patterning the MoS2 channel and source–drain electrodes, 5% P(VDF-TrFE) dissolved in dimethylformamide (DMF) was spin coated on the device surface at 3000 r/min for 1 min and then baked at 140 °C for 4 h to improve its crystallization. The achieved P(VDF-TrFE) ferroelectric film thickness was ~300 nm. Then the top gate electrodes (30 nm Au) were deposited followed by photolithography, and the ethylic acid was used in the lift-off process.

Characterization. Raman and PL measurement: The Raman shift and PL measurements were performed on a JY Horiba HR800 system. The wavelength of emission laser is 532 nm (spot size ~1 μm, power ~1 mW). The MoS2 FET was placed in a chip-carrier in the chamber and wire-bonded to the external measurement equipment. To achieve a long working distance, a 50X objective lens was used for laser focusing and signal collecting. The strain applied on the P(VDF-TrFE) piezo-electret was supplied with a motorized positioning system. Under each strain condition, more than 20 spots were measured for both Raman and PL spectra to reduce the measurement errors. The strain on P(VDF-TrFE) device was applied by a motorized positioning system. The detailed strain calculation followed: ε = Δt / L = (Δt0 + tRθ) − (Δt0 − tRθ) / L, where L0 and L are the original and strained length of the substrate, Δt and t are half.
thickness and curvature of the substrate, respectively. All the measurements of MoS2 FET electrical property gated by P(VDF-TrFE) were performed with a semiconductor analysis system (Agilent 1500A) under ambient conditions.

ASSOCIATED CONTENT

Supporting Information
The Supporting Information is available free of charge on the ACS Publications website at DOI: 10.1021/acsnano.8b07477.

Transfer property of MoS2 FET without P(VDF-TrFE); schematic diagram of the device back-gated by the P(VDF-TrFE); energy band bend and charge distribution in P(VDF-TrFE) with different polarization conditions; Raman shift and PL spectrum for monolayer MoS2 FET coated on MoS2; hysteresis of the device with P(VDF-TrFE) as gate material under different strains; piezoelectrical property of the P(VDF-TrFE) device; output property of MoS2 FET changed with the strain applied on the P(VDF-TrFE) film; gauge factor of the piezo-electret gate MoS2 FET strain sensor; measurement of the thickness of P(VDF-TrFE) spin-coated on MoS2 film; hysteresis of the device with P(VDF-TrFE) spin-coated on MoS2 film; instantaneous Pressure Visualization.

AUTHOR INFORMATION

Corresponding Authors
*E-mail: sunjun@binn.cas.cn.
*E-mail: zhong.wang@mse.gatech.edu.
*E-mail: gyzhang@iphy.ac.cn.

Notes
The authors declare no competing financial interest.

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